

PMG85XP 20 V, 2 A P-channel Trench MOSFET Rev. 1 — 28 June 2011

Product data sheet

1. **Product profile**

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

Low threshold voltage

Trench MOSFET technology

Very fast switching

1.3 Applications

Relay driver

High-speed line driver

High-side loadswitch

Switching circuits

1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$	<u>[1]</u>	-	-	-2	А
Static charact	eristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$		-	90	115	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		
2	D	drain	<u> </u>	D
3	G	gate		
4	S	source	0	
5	D	drain	□1 □2 □3	Ś
6	D	drain	SOT363 (TSSOP6)	017aaa094

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMG85XP	TSSOP6	plastic surface-mounted package; 6 leads	SOT363		

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMG85XP	YA%

[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$	<u>[1]</u>	-	-2	Α
		$V_{GS} = -4.5 \text{ V}; T_j = 100 \text{ °C}$	<u>[1]</u>	-	-1.3	Α
I _{DM}	peak drain current	$T_{amb} = 25$ °C; single pulse; $t_p \le 10 \mu s$		-	-8	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	375	mW
			<u>[1]</u>	-	725	mW
		T _{sp} = 25 °C		-	2400	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode					
Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-0.7	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

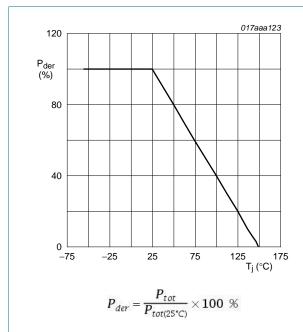
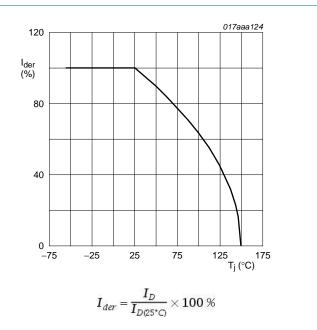
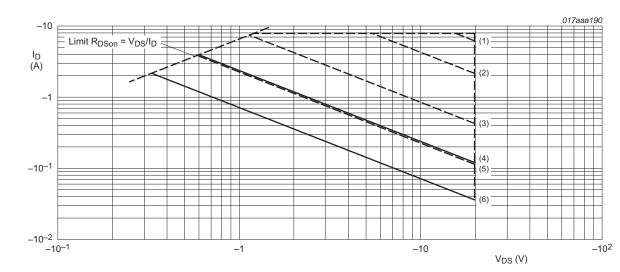


Fig 1. Normalized total power dissipation as a function of junction temperature



ig 2. Normalized continuous drain current as a function of junction temperature

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I_{DM} = single pulse

- (1) $t_p = 100 \, \mu s$
- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) DC; $T_{sp} = 25$ °C
- (5) $t_p = 100 \text{ ms}$
- (6) DC; T_{amb} = 25 °C; drain mounting pad 6 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	290	334	K/W
			[2]	-	150	173	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	45	52	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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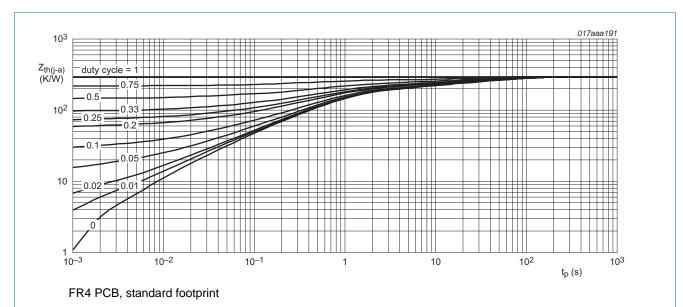


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

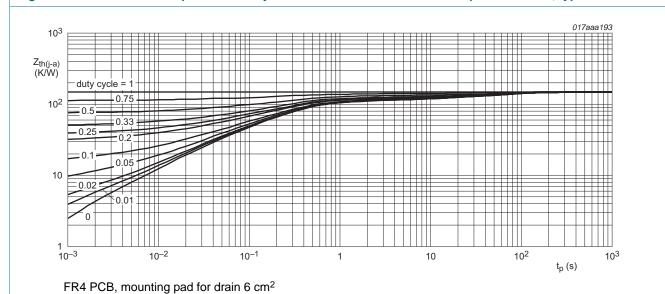


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

Table 1.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.65	-0.9	-1.15	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	-15	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$	-	90	115	mΩ
		$V_{GS} = -4.5 \text{ V}; I_D = -2 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	130	166	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$	-	125	160	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$	-	6.3	-	S
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -1 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	4.8	7.2	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	1.1	-	nC
Q_{GD}	gate-drain charge		-	1	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	560	-	pF
Coss	output capacitance	T _j = 25 °C	-	80	-	pF
C _{rss}	reverse transfer capacitance		-	55	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; V_{GS} = -4.5 V; $R_{G(ext)}$ = 6 Ω ;	-	13	-	ns
t _r	rise time	$T_j = 25 ^{\circ}\text{C}; I_D = -2.5 ^{\circ}\text{A}$	-	35	-	ns
$t_{d(off)}$	turn-off delay time		-	39	-	ns
t _f	fall time		-	25	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = -0.7 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_i = 25 \text{ °C}$	-	-0.7	-1.2	V

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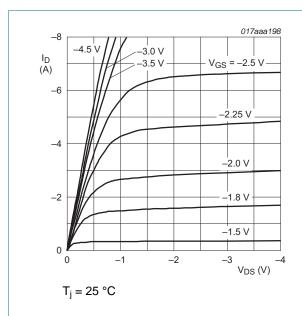
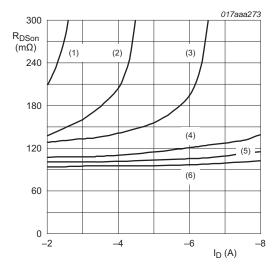


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T_i = 25 °C

(1) $V_{GS} = -2.0 \text{ V}$

(2) $V_{GS} = -2.25 \text{ V}$

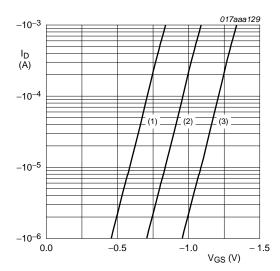
(3) $V_{GS} = -2.5 \text{ V}$

(4) $V_{GS} = -3.0 \text{ V}$

(5) $V_{GS} = -3.5 \text{ V}$

(6) $V_{GS} = -4.5 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



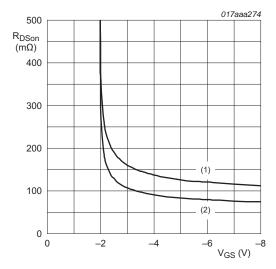
 $T_j = 25$ °C; $V_{DS} = -3$ V

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



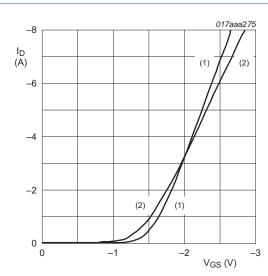
 $I_D = -2.5 A$

(1) $T_i = 125 \, ^{\circ}C$

(2) $T_j = 25 \, ^{\circ}\text{C}$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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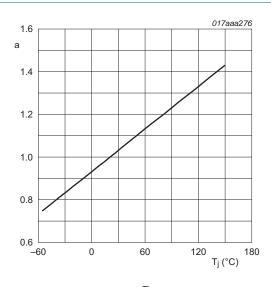


 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_j = 25 \, ^{\circ}C$$

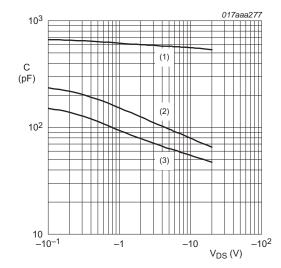
(2)
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



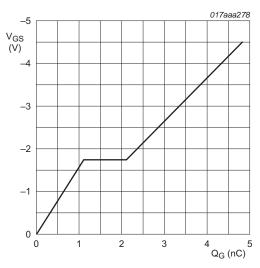
 $f = 1 MHz; V_{GS} = 0 V$

(1) C_{iss}

(2) C_{oss}

(3) C_{rss}

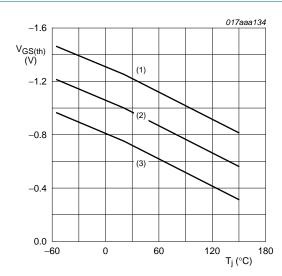
Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $I_D = -3 A$; $V_{DS} = -10 V$; $T_{amb} = 25 °C$

Fig 13. Gate-source voltage as a function of gate charge; typical values

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 I_D = -0.25 mA; V_{DS} = V_{GS}

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 14. Gate-source threshold voltage as a function of junction temperature

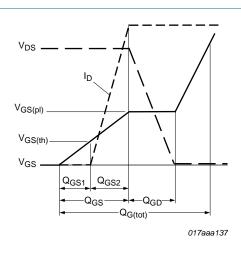
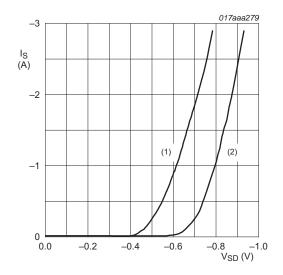


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

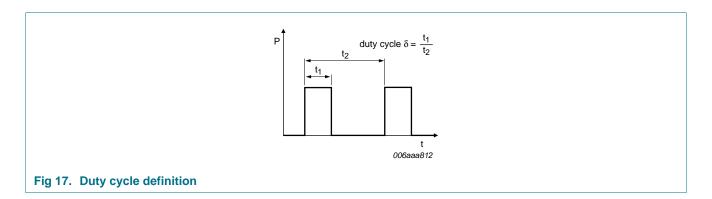
(1) $T_i = 150 \, ^{\circ}\text{C}$

(2) $T_j = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



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9. Package outline

Plastic surface-mounted package; 6 leads

SOT363

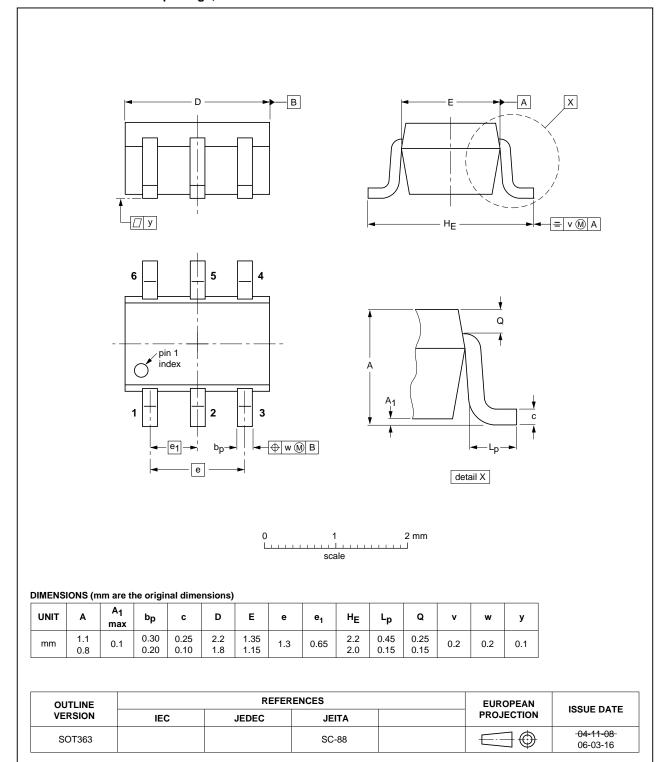
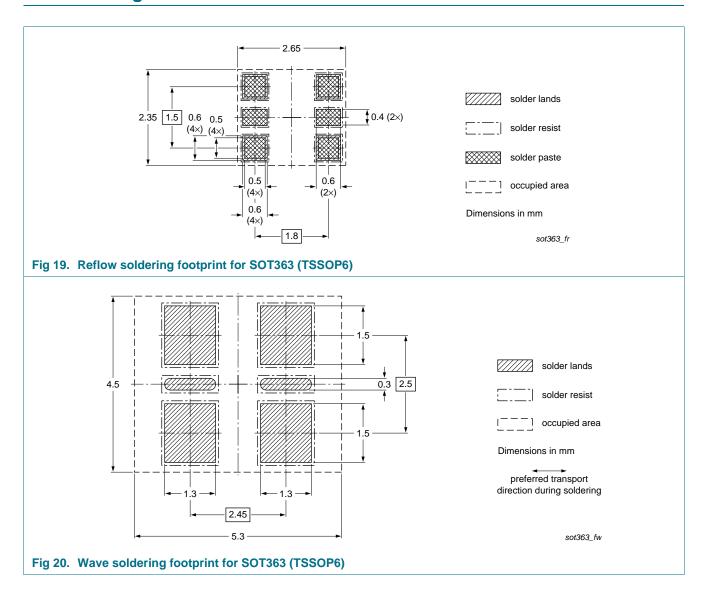


Fig 18. Package outline SOT363 (TSSOP6)

PMG85XE

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10. Soldering



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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMG85XP v.N	20110628	Product data sheet	-	-

20 V, 2 A P-channel Trench MOSFET

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12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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